VS-ENW30S120T

Vishay Semiconductors

EMIPAK 1B PressFit Power Module 1200 V Silicon Carbide Single Phase Bridge, 30 A



www.vishay.com

EMIPAK 1B (package example)

PRIMARY CHARACTERISTICS						
SINGLE PHASE BRIDGE						
V _{RRM}	1200 V					
V _{FM} typical at 30 A	1.35 V					
I _O at T _{SINK} = 138 °C	30 A					
Q _C typical at 30 A	118 nC					
Package	EMIPAK 1B					
Circuit configuration	SiC diodes full bridge					

FEATURES

resistance

- SiC diode technology
- Exposed Al₂O₃ substrate with low thermal



RoHS COMPLIANT

- Very high frequency operating
- Low internal inductances
- Qualified using AQG324 guideline as reference
- PressFit pins locking technology PATENT(S): <u>www.vishay.com/patents</u>
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION

The EMIPAK 1B package is easy to use thanks to the PressFit pins. The exposed substrate provides improved thermal performance.

The optimized layout also helps to minimize stray parameters, allowing for better EMI performance.

ABSOLUTE MAXIMUM RATINGS (T _J = 25 °C unless otherwise noted)								
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS				
Operating junction temperature	TJ		175	°C				
Storage temperature range	T _{Stg}		-40 to +150	U				
RMS isolation voltage	V _{ISOL}	T_J = 25 °C, all terminals shorted, f = 50 Hz, t = 1 s	3500	V				
SINGLE PHASE BRIDGE	SINGLE PHASE BRIDGE							
Maximum output current of bridge		180° conduction angle, T _{SINK} = 25 °C	67	А				
Maximum output current of bridge I _O		180° conduction angle, T _{SINK} = 80 °C	52	A				
Maximum peak one cycle forward	I _{FSM}	10 ms sine or 6 ms rectangular pulse, $T_J = 25 \ ^{\circ}C$, no voltage reapplied	230	А				
non-repetitive surge current		8.3 ms sine, $T_J = 25 \text{ °C}$, no voltage reapplied	241	А				
Maximum 1 ² t appability for fusing	l ² t	No voltage reapplied, t = 10 ms	265	A20				
Maximum I ² t capability for fusing	1-1	No voltage reapplied, t = 8.3 ms	240	A ² s				
Maximum I ² \sqrt{t} capability for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied 2645						

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
D1 - D4 SINGLE PHASE BRIDGE						
Forward voltage drop (per diode)	V	I _F = 30 A	-	1.35	1.82	v
Forward voltage drop (per diode)	V _{FM}	I _F = 30 A, T _J = 150 °C	-	1.79	-	v
Breakdown voltage (per diode)	V _{BR}	I _R = 1 mA	1200	-	-	V
Reverse leakage current (per diode)	I _{RM}	V _R = 1200 V	-	75	800	
neverse leakage current (per diode)		$V_{\rm R}$ = 1200 V, $T_{\rm J}$ = 150 °C	-	900	-	μA

PATENT(S): www.vishay.com/patents

This Vishay product is protected by one or more United States and international patents.

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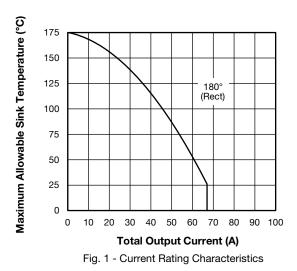
SWITCHING CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise noted)							
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		TYP.	MAX.	UNITS	
D1 - D4 SINGLE PHASE BRIDGE							
Total capacitive charge (per diode)	Q _C	V _R = 800 V, dl/dt = 500 A/µs	-	118	-	nC	
Total capacitance (per diode) C	C	V _R = 1 V, f = 1 MHz	-	2780	-	ρF	
	V _R = 800 V, f = 1 MHz	-	253	-	рг		

INTERNAL NTC - THERMISTOR SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUE	UNITS		
Desistance	R ₂₅	T _C = 25 °C	5000	0		
Resistance	R ₁₀₀	T _C = 100 °C	493 ± 5 %	Ω		
B-value	B _{25/50}	R ₂ = R ₂₅ exp. [B _{25/50} (1/T2 - 1/298.15K))]	3375 ± 5 %	К		
Maximum operating temperature			220	°C		
Dissipation constant			2	mW/°C		
Thermal time constant			8	S		

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS		
SINGLE PHASE BRIDGE - Thermal resistance junction to sink (per diode) ⁽¹⁾	R _{thJS}	-	0.90	-	°C/W		
Case to sink thermal resistance (per module) ⁽¹⁾		-	0.1	-	0/10		
Mounting torque (M4)		2	-	3	Nm		
Weight		-	28	-	g		

Note

 $^{(1)}$ $\,$ Mounting surface flat, smooth, and greased, λ_{grease} = 0.67 W/mK



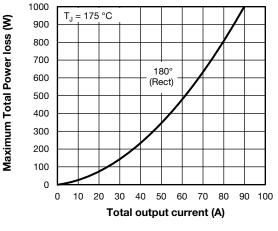
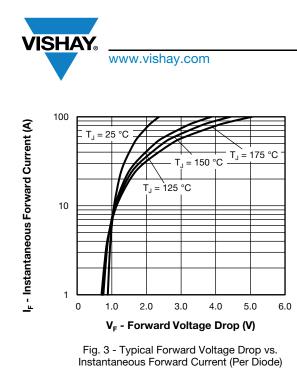


Fig. 2 - Total Power Loss Characteristics

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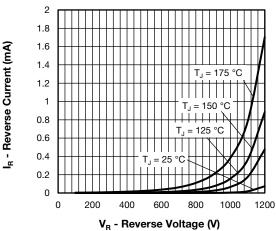


Fig. 4 - Typical Reverse Current vs. Reverse Voltage (Per Diode)

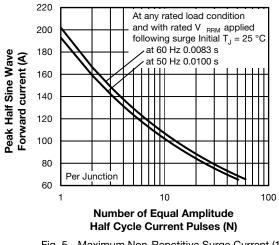


Fig. 5 - Maximum Non-Repetitive Surge Current (1)

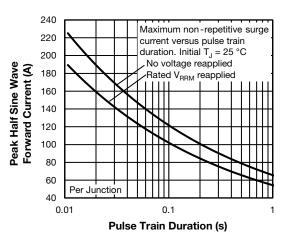


Fig. 6 - Maximum Non-Repetitive Surge Current (2)

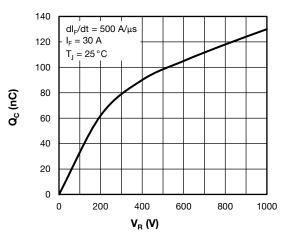


Fig. 7 - Total Capacitance Charge vs. Reverse Voltage (Per Diode)

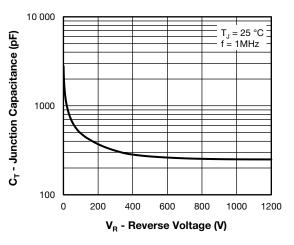


Fig. 8 - Typical Junction Capacitance vs. Reverse Voltage (Per Diode)

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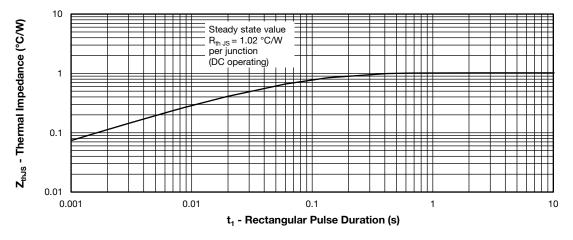
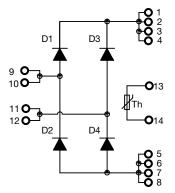


Fig. 9 - Z_{thJS} Thermal Impedance Characteristic (Per Diode)

ORDERING INFORMATION TABLE

Device code	VS-	EN	W	30	S	120	т	
		2	3	4	5	6	7	
	1 - 2 - 3 - 4 - 5 - 6 - 7 -	Pac Circ Cur Die Volt	hay Sem kage ind cuit confi rent ratif technolo age rati thermis	dicator (iguratior ng (30 = ogy (S = ng (120	EN = EI n (W = S : 30 A) : SiC dia	MIPAK ⁻ SiC diod ode)	1B) es full br	ridge)

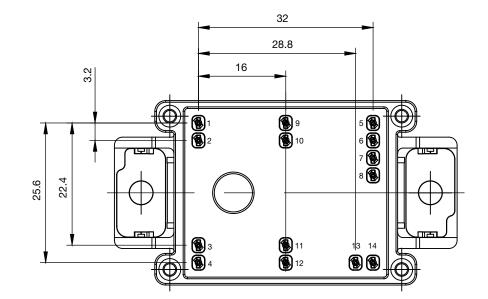
CIRCUIT CONFIGURATION



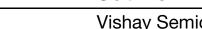




PACKAGE



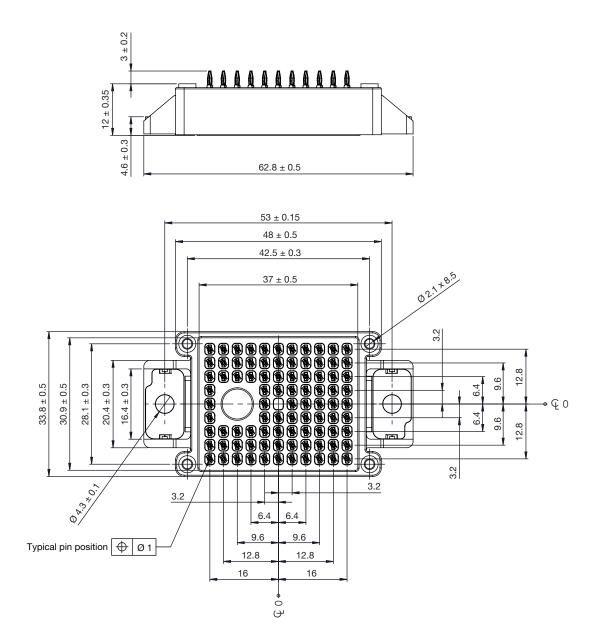
LINKS TO RELATED DOCUMENTS					
Dimensions www.vishay.com/doc?95558					
Application Note	www.vishay.com/doc?95580				





EMIPAK-1B PressFit

DIMENSIONS in millimeters





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